

**R1LV16****R1LV5256****R1R**

# RM L V 04 16 E G SB - 4 S 2 #A A 0

**RENESAS  
Memory****Chip configuration  
of LPSRAM**

L	Single chip
W	Two chips

**Operation Voltage**

V	3V
P	5V

**Memory density**

04	4Mb
08	8Mb
16	16Mb

**Bit configuration**

08	x8
16 or 14	x16 or x8/x16 (Byte# control)

**Chip generation****Industrial Grade****Package type**

SA	sTSOP (4Mb) / TSOPI (8Mb/16Mb)
SB	TSOPII
SD	μTSOPII
SP	SOP
BG	FBGA

**Specification**

0	Standard
---	----------

**Environment**

A	Lead free
C	Lead free(FBGA)

**Packing**

A	Tray
C	Tube
H	Embossed Tape (TSOP, SOP)
K	Embossed Tape (FBGA, sTSOP)

**Operating Temperature**

2	-40 to 85 deg C
---	-----------------

**Stand-by current /  
Data retention current**

S	Standard
---	----------

**Access time**

5	55ns
4	45ns

**Example shown here : Part number RMLV0416EGSB-4S2#AA0**

## Low Power SRAM(0.11um) (4Mbit, 8Mbit, 16Mbit)

# R1 L V 16 16 R SD - 7 S I #B0

RENASAS  
Memory

Chip configuration  
of LPSRAM

L	Single chip
W	Two chips

Operation Voltage

V	3V
P	5V

Memory density

01	1Mb
02	2Mb
04	4Mb
08	8Mb
16	16Mb
32	32Mb
64	64Mb

Bit configuration

08	x8
16	x16 or x8/x16 (Byte# control)

Chip generation

Packing, Environmental

	Packing	Environmental
#B0	Tray or Tube	Pb free
#S0	Embossed Tape	Pb free

Operating Temperature

R	0 to 70 deg C
I	-40 to 85 deg C

Access time

7	70 ns
5	55ns
4	45ns

Stand by current /  
Data retention current

L	Standard
S	Low power version

Package type

SA	sTSOP (1Mb/2Mb/4Mb) TSOPI (8Mb/16Mb/32Mb/64Mb)
SB	TSOPII
SD	μTSOPII
SF	TSOPI (1Mb)
SP	SOP(4Mb)
SN	SOP(1Mb)
BG	FBGA

Example shown here:

Part number R1LV1616RSD-7SI#B0

Low Power SRAM(0.15um) (1Mbit, 2Mbit, 4Mbit, 8Mbit, 16Mbit, 32Mbit, 64Mbit)

# R1 L V 5256 E SP - 7 S I #B0

**RENESAS  
Memory**

**Chip configuration  
of LPSRAM**

<b>L</b>	Single chip
----------	-------------

**Operation Voltage**

<b>V</b>	3V
<b>P</b>	5V

**Memory density & bit configuration**

	density	bit configuration
<b>5256</b>	256Kb	x8

**Chip generation**

**Packing, Environmental**

	Packing	Environmental
<b>#B0</b>	Tray or Tube	Pb free
<b>#S0</b>	Embossed Tape	Pb free

**Operating Temperature**

<b>R</b>	0 to 70 deg C
<b>I</b>	-40 to 85 deg C

**Stand by current / Data retention current**

<b>L</b>	Standard
<b>S</b>	Low power version

**Access time**

<b>7</b>	70 ns
<b>5</b>	55ns

**Package type**

<b>SA</b>	TSOPI (13.4mm x 8mm)
<b>SP</b>	SOP

## Low Power SRAM (256Kbit)

Example shown here : Part number **R1LV5256ESP-7SI#B0**

# R1 R W 04 16 D SB - 2 P I #B0

RENESAS  
Memory  
Fast SRAM

**Packing, Environmental**

	Packing	Environmental
#B0	Tube(SOJ)	Pb free
#D0	Tray(TSOP)	Pb free
#S0	Embossed Tape	Pb free

**Operation Voltage**

W	3.3V
P	5V

**Operating Temperature**

R	0 to 70 deg C
I	-40 to 85 deg C

**Memory density**

04	4Mb
----	-----

**Stand by current / Data retention current**

P	Standard
L	Low power version
S	Super Low power version

**Bit configuration**

08	x8
16	x16

**Access time**

2	12 ns
0	10 ns

**Chip generation**

**Package type**

GE	SOJ
SB	TSOP II

## 4Mbit Fast SRAM

Example shown here: Part number R1RW0416DSB-2PI#B0